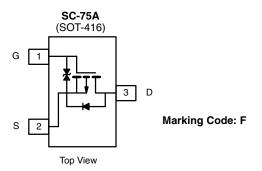




P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY				
$V_{DS(min.)}(V)$ $R_{DS(on)}(\Omega)$		V _{GS(th)} (V)	I _D (mA)	
- 60	4.0 at V _{GS} = - 10 V	- 1 to 3.0	- 190	



Ordering Information: Si1021R-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES





ROHS COMPLIANT HALOGEN FREE

- TrenchFET® Power MOSFETs
- · High-Side Switching
- Low On-Resistance: 4 Ω
- Low Threshold: 2 V (typ.)
- Fast Switching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Miniature Package
- ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- · Battery Operated Systems
- Power Supply Converter Circuits
- · Solid-State Relays

BENEFITS

- · Ease in Driving Switches
- · Low Offset Voltage
- Low-Voltage Operation
- · High-Speed Circuits
- · Easily Driven without Buffer
- Small Board Area

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 60	V	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current /T 150 °C\8	T _A = 25 °C		- 190		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C	l _D	- 135	mA	
Pulsed Drain Current ^b		I _{DM}	- 650		
Power Dissipation ^a	T _A = 25 °C	В	250	mW	
Power Dissipation	T _A = 85 °C	P _D	130]	
Maximum Junction-to-Ambient ^a		R _{thJA}	500	°C/W	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

Notes:

- a. Surface mounted on FR4 board.
- b. Pulse width limited by maximum junction temperature.

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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_{D} = -10 \mu\text{A}$	- 60		V		
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -0.25 \text{ mA}$	- 1		- 3.0	V	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 10	μΑ	
Gate-Body Leakage	Lance	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$		± 200			
Gale-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			± 500	nA	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			± 100		
Zara Cata Valtaga Drain Current		V _{DS} = - 50 V, V _{GS} = 0 V			- 25	- 25 - 250	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 50 V, V _{GS} = 0 V, T _J = 85 °C			- 250		
On State Drain Correcti		V _{DS} = -10 V, V _{GS} = - 4.5 V	- 50			mA	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = -10 V, V _{GS} = - 10 V	- 600				
Drain-Source On-State Resistance ^a		V _{GS} = - 4.5 V, I _D = - 25 mA			8	8	
	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 500 mA			4 Ω		
		V _{GS} = - 10 V, I _D = - 500 mA, T _J = 125 °C			6	†	
Forward Transconductance	9 _{fs}	V _{DS} = - 10 V, I _D = - 100 mA	80			mS	
Diode Forward Voltage ^a	V _{SD}	V _{DS} = - 200 mA, V _{GS} = 0 V	80			V	
Dynamic							
Total Gate Charge	Qg			1.7		nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -15 \text{ V}, I_{D} \cong -500 \text{ mA}$		0.26			
Gate-Drain Charge	Q _{gd}			0.46			
Input Capacitance	C _{iss}			23			
Output Capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		10		pF	
Reverse Transfer Capacitance	C _{rss}			5			
Switching ^b							
Turn-On Time	t _{ON}	V _{DD} = - 25 V, R _L = 150 Ω,		20		ns	
Turn-Off Time	t _{OFF}	$I_D \cong$ - 200 mA, $V_{GEN} =$ - 10 V, $R_g =$ 10 Ω		35			

Notes:

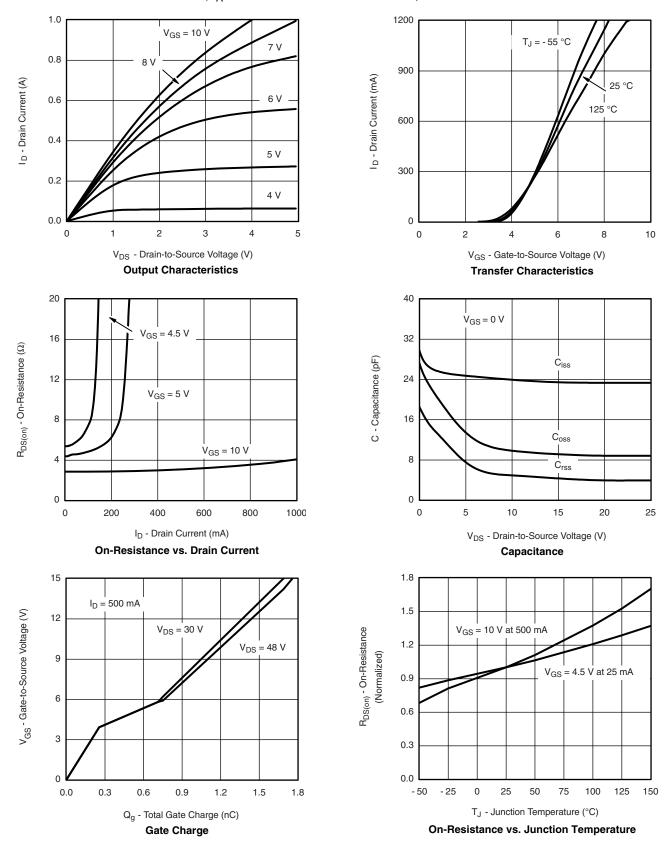
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.

b. Switching time is essentially independent of operating temperature.



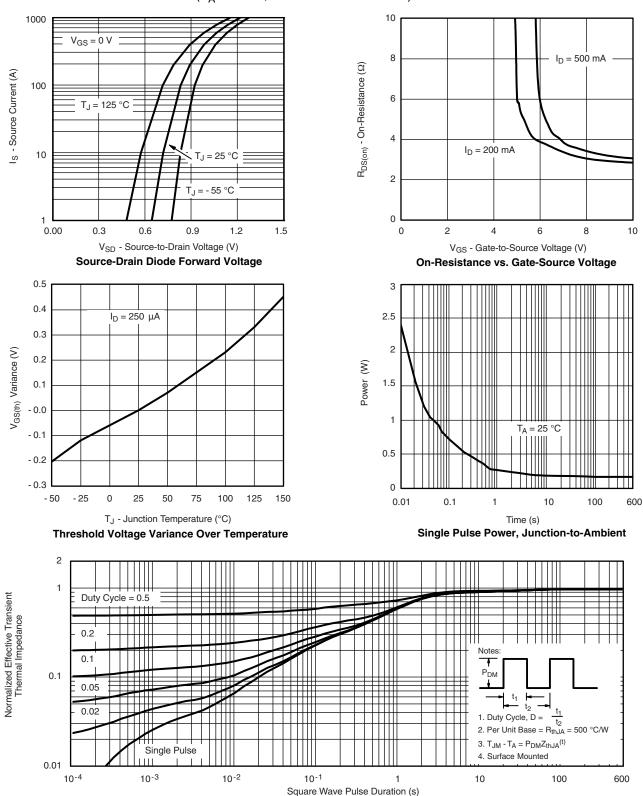
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

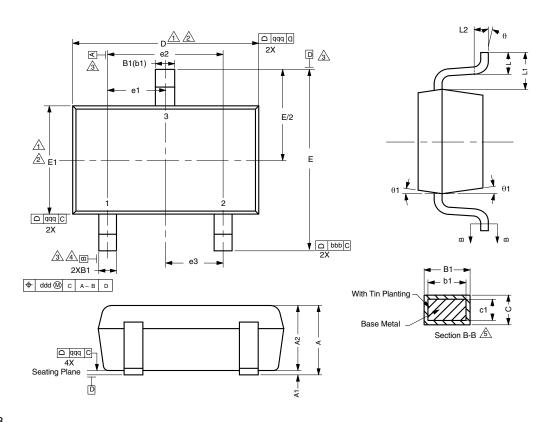


Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71410.



SC-75A: 3 Leads



DWG: 5868

Notes

Dimensions in millimeters will govern.

- Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.
- Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
- ②Datums A, B and D to be determined 0.10 mm from the lead tip.

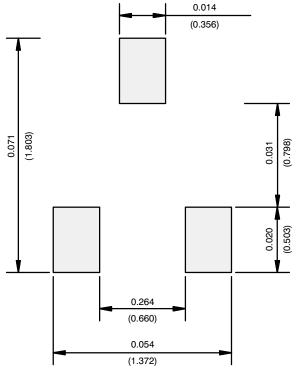
 4\text{Terminal positions are shown for reference only.}
- These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIMENSIONS	TOLERANCES		
aaa	0.10		
bbb	0.10		
ccc	0.10		
ddd	0.10		

DIM.	MILLIMETERS			NOTE
DIIVI.	MIN.	NOM.	MAX.	NOTE
Α	-	-	0.80	
A1	0.00	-	0.10	
A2	0.65	0.70	0.80	
B1	0.19	-	0.24	5
b1	0.17 - 0.21		0.21	
С	0.13	-	0.15	5
c1	0.10	-	0.12	5
D	1.48	1.575	1.68	1, 2
E	1.50	1.60	1.70	
E1	0.66	0.76	0.86	1, 2
e1	0.50 BSC			
e2	1.00 BSC			
e3	0.50 BSC			
L	0.15	0.205	0.30	
L1	0.40 ref.			
L2	0.15 BSC			
q	0°	-	8°	
q1	4°	-	10°	



RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

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